

**AMENDMENTS TO THE CLAIMS**

1. (Previously Presented) A method for forming a pattern, comprising:  
providing a substrate on which a plurality of unit panels and etching object layers on the respective unit panel areas are formed;  
dividing the substrate into at least two areas, each of the two areas having at least one unit panel;  
providing a cliché on which a plurality of grooves are formed, the cliché being divided into a plurality of areas corresponding to the divided areas of the substrate;  
filling resist in the grooves;  
transferring the resist in the grooves of one area of the cliché on a blanket applied on a surface of a printing roll by contacting and rotating the printing roll with the blanket on the cliché, the printing roll corresponding to the divided area of the substrate; and  
applying the resist transferred on the surface of the blanket on the etching object layer on the area of the substrate corresponding to the area of the cliché.

2. (Previously Presented) The method of claim 1, wherein the printing roll has a same width as that of the divided area of the substrate.

3. (Canceled)

4. (Previously Presented) The method of claim 2, wherein a length of the blanket is the same as a length of a circumference of the printing roll, which is same as a length of the divided area of the substrate.

5. (Original) The method of claim 1, wherein the divided area of the substrate includes one or more unit panels.

6. (Original) The method of claim 1, wherein the cliché is formed to have a same size as that of the divided area of the substrate.

7. (Original) The method of claim 1, wherein the printing roll is formed to have a same size as that of the divided area on the substrate.

8. (Original) The method of claim 1, wherein the etching object layer includes a metal layer.

9. (Original) The method of claim 1, wherein the etching object layer includes an insulating layer comprised of SiO<sub>x</sub> or SiN<sub>x</sub>.

10. (Original) The method of claim 1, wherein the etching object layer is a semiconductor layer.

11. ( Previously Presented) A method for forming a pattern, comprising:

providing a substrate on which a plurality of unit panels and etching object layers on the respective unit panel areas are formed;

dividing the substrate into a plurality of divided areas so as to include at least one or more unit panels;

providing a cliché on which a plurality of grooves are formed, the cliché being divided into a plurality of areas corresponding to the divided areas of the substrate;

filling resist in the grooves of the cliché;

providing a blanket on a printing roll having a same width as that of the divided area of the substrate;

transferring the resist filled in the grooves of the divided area of the cliché onto a surface of the blanket on the printing roll by contacting and rotating the printing roll with the blanket on the divided area of the cliché corresponding to the divided area of the substrate; and

applying the resist transferred on the surface of the blanket on the etching object layer on the area of the substrate corresponding to the divided area of the cliché.

12. (Previously Presented) The method of claim 11, wherein applying the resist on the etching object layer is performed by contacting the resist transferred on the surface of the blanket on the printing roll on the substrate and by rotating the printing roll with the blanket.

13. (Original) The method of claim 11, wherein the divided area of the substrate includes at least one unit panel.

14. (Original) The method of claim 11, wherein the etching object layer includes a metal layer.

15. (Original) The method of claim 11, wherein the etching object layer comprises an insulating layer comprised of SiO<sub>x</sub> or SiN<sub>x</sub>.

16. (Original) The method of claim 11, wherein the etching object layer is a semiconductor layer.

17-27. (Canceled)

28. (Previously Presented) The method of claim 1, wherein the blanket improves adhesive force with the resist.

29. (Previously Presented) The method of claim 11, wherein the blanket improves adhesive force with the resist.

30. (Canceled)

31. (Canceled)

32. (Canceled)